

Light-emitting Semiconductor device Having Enhanced Brightness

Abstract of the Disclosure

This invention provides a light-emitting semiconductor device having enhanced brightness, to ensure even current distribution emitted by a front contact of the light emitting diodes so as to improve the light-emitting efficiency of the active layer. This invention adopts the method to manufacture the light-emitting device, comprising the steps of: forming an active layer on a substrate; forming a capping layer on the active layer to enhance current distribution, where a back contact is located on another side of the substrate and a front contact is located above the capping layer. This invention is characterized by: re-designing the front contact, by reducing the width of a metallic pattern constructing fingers or Mesh lines and increasing the number of the fingers or Mesh lines, so as to resolve the current crowding problem.